

5419,883

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
30 September 2004 (30.09.2004)

PCT

(10) International Publication Number
WO 2004/084405 A2

(51) International Patent Classification⁷:

H03H

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(21) International Application Number:

PCT/IB2004/000772

(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN, CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM, ZW.

(22) International Filing Date: 17 March 2004 (17.03.2004)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

03100736.2

21 March 2003 (21.03.2003) EP

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

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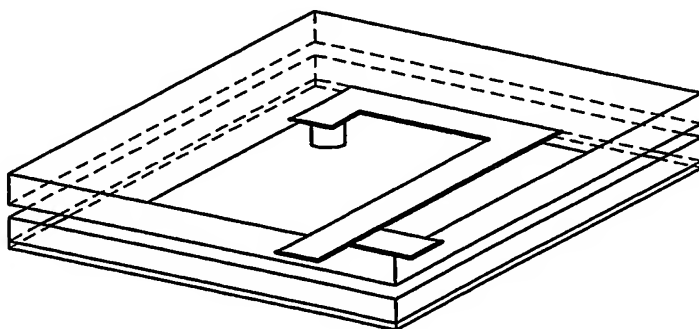
Published:

— without international search report and to be republished upon receipt of that report

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.

(54) Title: MULTILAYER STACK WITH COMPENSATED RESONANT CIRCUIT

$$\frac{w}{h_1} > 3 \quad (I)$$



(57) Abstract: A metallization structure in a multilayer stack, which is arranged at a distance from a ground electrode, is characterized in that the metallization structure has a capacitor electrode and a line that acts as a coil, where the capacitor electrode and the line are arranged in a common plane which lies parallel with the ground electrode at a distance h_1 , and in that formula (I) where w is the width of the line.

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